

Features

- High reliability
- General purpose leads
- Peak wavelength λp=850nm
- Mechanically and spectrally matched to the phototransistor
- Low forward voltage
- High radiant intensity

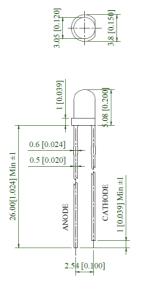
Applications

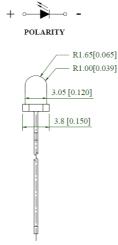
- Optoelectronic Switch
- IR Touch-Panel
- Industrial IR Equipment
- Consumer Electronics
- High Speed IR Communications

Description

- The infrared emitting diode (850nm) is a high intensity diode, molded in a water clear transparent plastic package.
- The device is spectrally matched with silicon photodiode and phototransistor.

Package Dimensions in mm





Notes:

- 1. All dimensions are in millimeters (inches).
- 2. Tolerance is \pm 0.25 mm (.010 $^{\prime\prime}$) unless otherwise noted.

Figure 1. INL-3AIR30 Package Dimensions



Absolute Maximum Rating at 25°C (Note 1)

Product	Emission Color	P _d (mW)	I _F (mA)	I _{FP} * (A)	V _R (V)	T _{OP} (°C)	T _{ST} (°C)
INL-3AIR30	Infrared	160	100	1	5	-40°C~+80°C	-40°C~+85°C

Notes

1. Condition for IFP is pulse of 1/10 duty and 1kHz frequency

Electrical Characteristics $T_A = 25^{\circ}$ (Note 1)

	Emission		V _F (V)		λ(nm)			Viewing Angle	Ee(mW/sr)	
Product	Color	l _F (mA)	min	max	λ_{D}	λ_{P}	$ riangle \lambda$	2 <i>0</i> 1/2	min	typ.
INL-3AIR30	Infrared	20	1.0	1.6	-	850	45	30	6	12

Notes

1. Performance guaranteed only under conditions listed in above tables.

ESD Precaution

ATTENTION: Electrostatic Discharge (ESD) protection

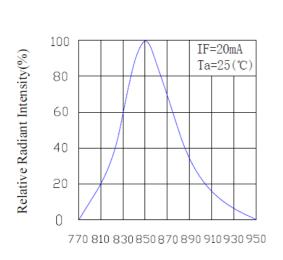
The symbol above denotes that ESD precaution is needed. ESD protection for GaP and AlGaAs based chips is necessary even though they are relatively safe in the presence of low static-electric discharge. Parts built with AlInGaP, GaN, or/and InGaN based chips are STATIC SENSITIVE devices. ESD precaution must be taken during design and assembly. If manual work or processing is needed, please ensure the device is adequately protected from ESD during the process.

Please be advised that normal static precautions should be taken in the handling and assembly of this device to prevent damage or degradation which may be induced by electrostatic discharge (ESD).



INL-3AIR30 5mm Infrared Emitting Diode Though Hole Lamp LED

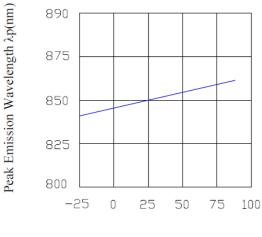
Typical Characteristic Curves



Spectral Distribution

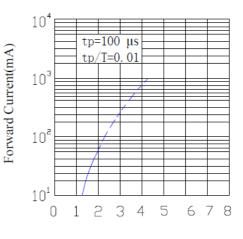
Wavelength $\lambda(nm)$

Peak Emission Wavelength & Ambient Temperature



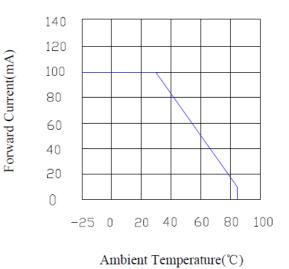
Ambient Temperature(°C)

Forward Current & Forward Voltage

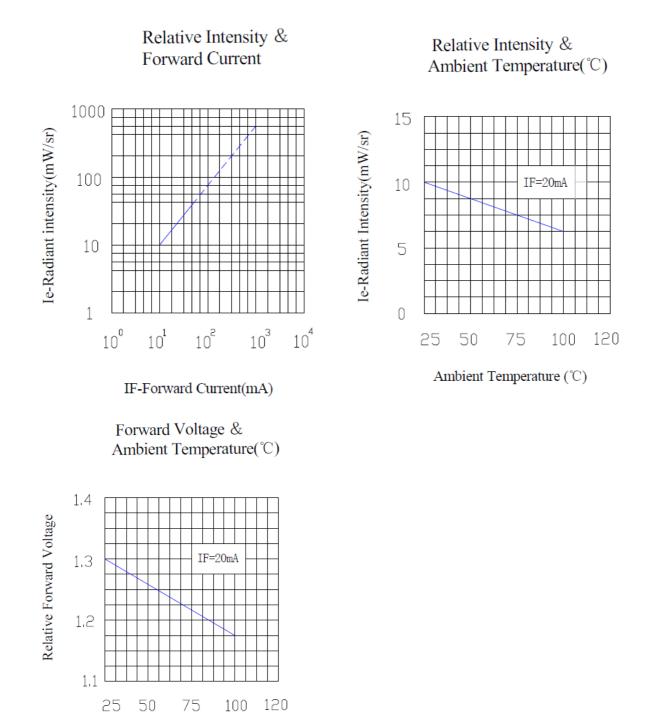


Forward Voltage(V)

Forward Current & Ambient Temperature



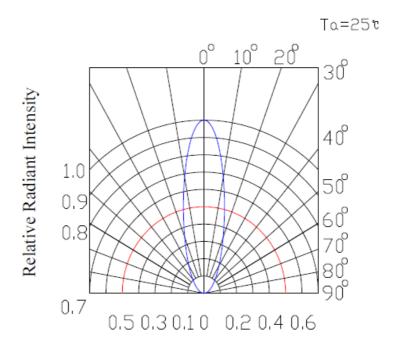




Ambient Temperature (°C)



Typical Characteristic Curves – Radiation Pattern

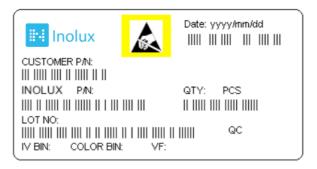


Ordering Information

Product	Emission Color	Technology	Test Current I⊧ (mA)	Radiant Intensity Ee (mW/sr) (Typ.)	Forward Voltage V _F (V) (Typ.)	Orderable Part Number
INL-3AIR30	Infrared	AlGaAs	20	12	1.4	INL-3AIR30



Label Specifications



Inolux P/N:

I	١	N	L	-	3	А	-	IR	3	0		х	х	х	Х
		·		Package		Lens	Color	View Angle			Customized Stamp-off				
La		blux o Typ			stan	۹ = dard ۱m	(Blank) = clear	IR = 850nm	30 =	· 30 deg.					

Lot No.:

Z	2	0	1	7	01	24	001
Internal		Year (2017	2018)	Month	Date	Serial	
Tracker			, 2018,)	WOITCH	Date	Serial	



Reliability

Item	Frequency/ lots/ samples/ failures	Standards Reference	Conditions		
Precondition	For all reliability monitoring tests according to JEDEC Level 2	J-STD-020	1.) Baking at 85°C for 24hrs 2.) Moisture storage at 85°C/ 60% R.H. for 168hrs		
Solderability	1Q/ 1/ 22/ 0	JESD22-B102-B And CNS-5068	Accelerated aging 155°C/ 24hrs Tinning speed: 2.5+0.5cm/s Tinning: A: 215°C/ 3+1s or B: 260°C/ 10+1s		
Resistance to soldering heat		CNS-5067	Dipping soldering terminal only Soldering bath temperature A: 260+/-5°C; 10+/-1s B: 350+/-10°C; 3+/-0.5s		
Operating life test	1Q/ 1/ 40/ 0	CNS-11829	 Precondition: 85°C baking for 24hrs 85°C/ 60%R.H. for 168hrs Tamb25°C; IF=20mA; duration 1000hrs 		
High humidity, high temperature bias	1Q/ 1/ 45/ 0	JESD-A101-B	Tamb: 85°C Humidity: 85% R.H., IF=5mA Duration: 1000hrs		
High temperature bias	1Q/ 1/ 20	IN specs.	Tamb: 55°C IF=20mA Duration: 1000hrs		
Pulse life test	1Q/ 1/ 40/ 0		Tamb25°C, If=20mA,, Ip=100mA, Duty cycle=0.125 (tp=125 μ s,T=1sec) Duration 500hrs)		
Temperature cycle	1Q/ 1/ 76/ 0	JESD-A104-A IEC 68-2-14, Nb	A cycle: -40 degree C 15min; +85 degree C 15min Thermal steady within 5 min 300 cycles 2 chamber/ Air-to-air type		
High humidity storage test	1Q/ 1/ 40/ 0	CNS-6117	60+3°C 90+5/-10% R.H. for 500hrs		
High temperature storage test	1Q/ 1/ 40/ 0	CNS-554	100+10°C for 500hrs		
Low temperature storage test	1Q/ 1/ 40/ 0	CNS-6118	-40+5°C for 500hrs		



Revision History

Changes since last revision	Page	Version No.	Revision Date
Initial Release		1.0	01-19-2019

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2. A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

Mouser Electronics

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Inolux: INL-3AIR30